DATA SHEET

NEC

NPN SILICON GERMANIUM RF TRANSISTOR

2SC5761

NPN SiGe RF TRANSISTOR FOR LOW NOISE · HIGH-GAIN AMPLIFICATION FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M04)

FEATURES

- Ideal for low noise · high-gain amplification
- ★ NF = 0.9 dB TYP. @ V_{CE} = 2 V, I_C = 5 mA, f = 2 GHz
- Maximum stable power gain: MSG = 20.0 dB TYP. @ V_{CE} = 2 V, I_C = 20 mA, f = 2 GHz
- SiGe technology (f_T = 60 GHz, f_{max} = 60 GHz)
- Flat-lead 4-pin thin-type super minimold (M04) package

ORDERING INFORMATION

Part Number	Quantity	Supplying Form
2SC5761	50 pcs (Non reel)	• 8 mm wide embossed taping
2SC5761-T2	3 kpcs/reel	• Pin 1 (Emitter), Pin 2 (Collector) face the perforation side of the tape

Remark To order evaluation samples, contact your nearby sales office.
The unit sample quantity is 50 pcs.

ABSOLUTE MAXIMUM RATINGS (T_A = +25°C)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	8.0	V
Collector to Emitter Voltage	V_{CEO}	2.3	V
Emitter to Base Voltage	V_{EBO}	1.2	V
Collector Current	I_C	35	mA
Total Power Dissipation	P_{tot} Note	80	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	–65 to +150	°C

Note Mounted on 1.08 $cm^2 \times$ 1.0 mm (t) glass epoxy substrate

THERMAL RESISTANCE

Parameter	Symbol	Value	Unit
Junction to Case Resistance	$R_{th\ (j\text{-}c)}$	150	°C/W

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

Document No. PU10212EJ02V0DS (2nd edition)
Date Published May 2003 CP(K)
Printed in Japan

The mark ★ shows major revised points.

ELECTRICAL CHARACTERISTICS (T_A = +25°C)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Collector Cut-off Current	I_{CBO}	V_{CB} = 5 V, I_E = 0 mA	–	–	200	nA
Emitter Cut-off Current	I_{EBO}	V_{BE} = 0.5 V, I_C = 0 mA	–	–	200	nA
DC Current Gain	h_{FE} Note 1	V_{CE} = 2 V, I_C = 5 mA	200	–	400	–
RF Characteristics						
Insertion Power Gain	$\|S_{21e}\|^2$	V_{CE} = 2 V, I_C = 20 mA, f = 2 GHz	16.0	18.0	–	dB
Noise Figure	NF	V_{CE} = 2 V, I_C = 5 mA, f = 2 GHz, $Z_S = Z_{opt}$	–	0.9	1.1	dB
Reverse Transfer Capacitance	C_{re} Note 2	V_{CB} = 2 V, I_E = 0 mA, f = 1 MHz	–	0.17	0.22	pF
Maximum Stable Power Gain	MSG Note 3	V_{CE} = 2 V, I_C = 20 mA, f = 2 GHz	18.0	20.0	–	dB
Gain 1 dB Compression Output Power	$P_{O\ (1\ dB)}$	V_{CE} = 2 V, I_C = 20 mA, f = 2 GHz	–	12.0	–	dBm
3rd Order Intermodulation Distortion Output Intercept Point	OIP_3	V_{CE} = 2 V, I_C = 20 mA, f = 2 GHz	–	22.0	–	dBm

Notes 1. Pulse measurement: PW ≤ 350 μs, Duty Cycle ≤ 2%

2. Collector to base capacitance when the emitter grounded

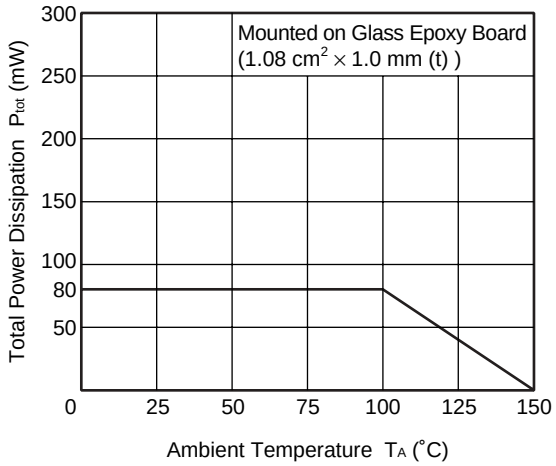
3. $MSG = \left| \frac{S_{21}}{S_{12}} \right|$

h_{FE} CLASSIFICATION

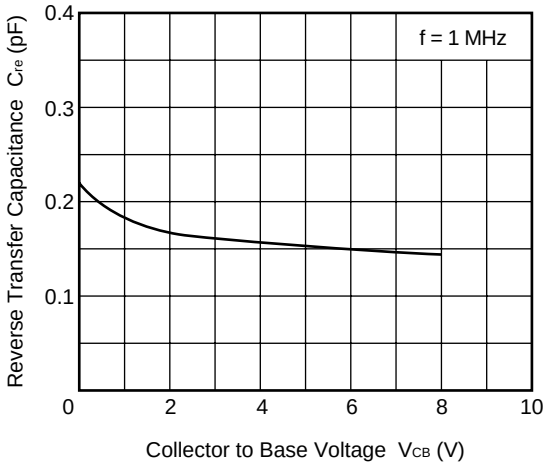
Rank	FB
Marking	T16
h_{FE} Value	200 to 400

TYPICAL CHARACTERISTICS (T_A = +25°C, unless otherwise specified)

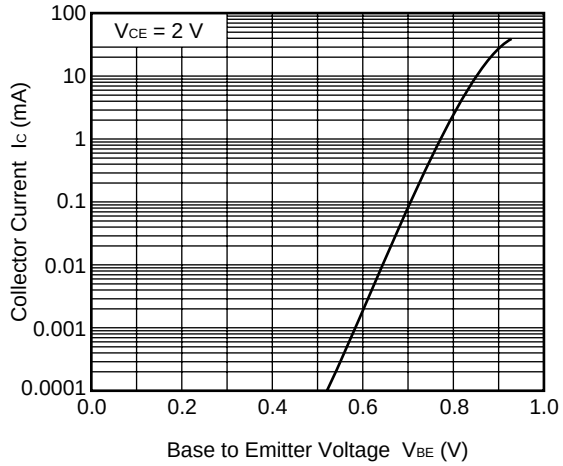
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



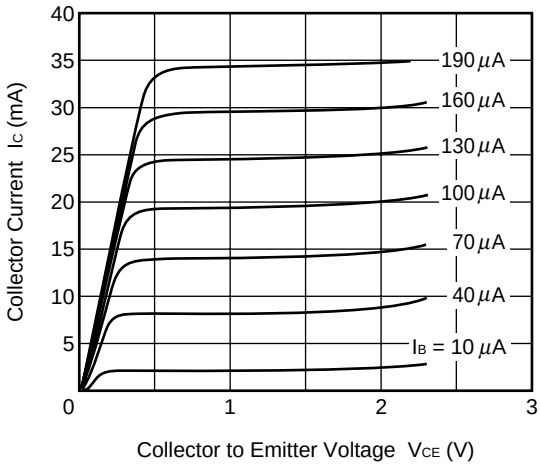
REVERSE TRANSFER CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



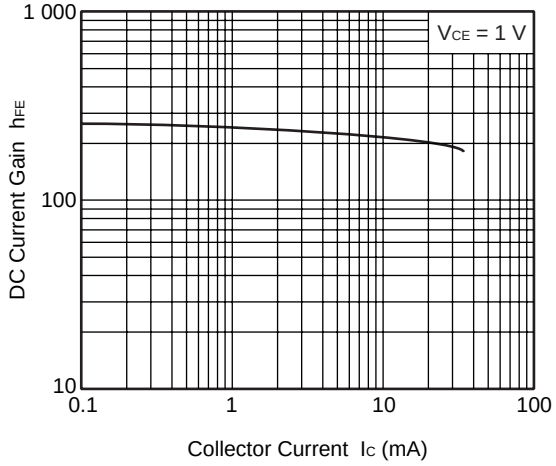
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



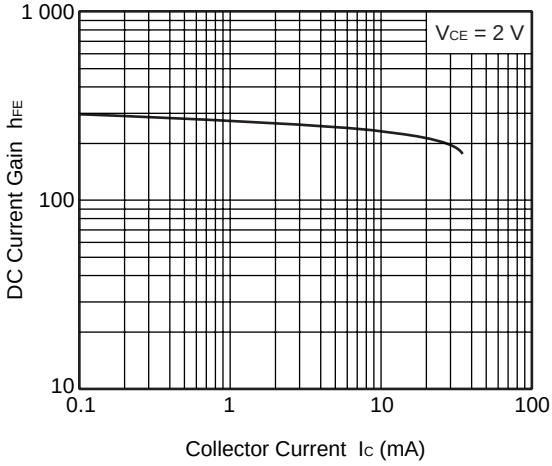
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



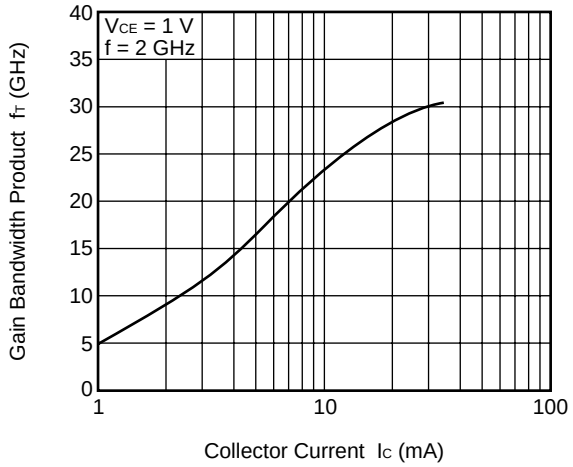
DC CURRENT GAIN vs. COLLECTOR CURRENT



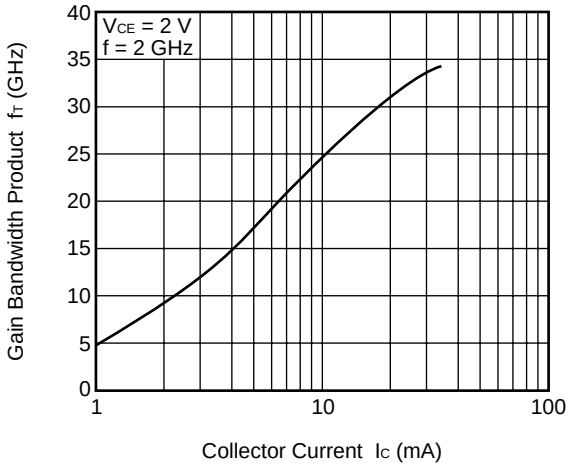
DC CURRENT GAIN vs. COLLECTOR CURRENT



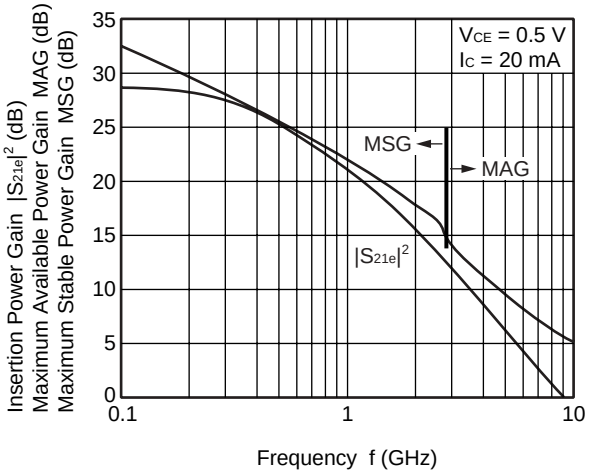
GAIN BANDWIDTH PRODUCT
vs. COLLECTOR CURRENT



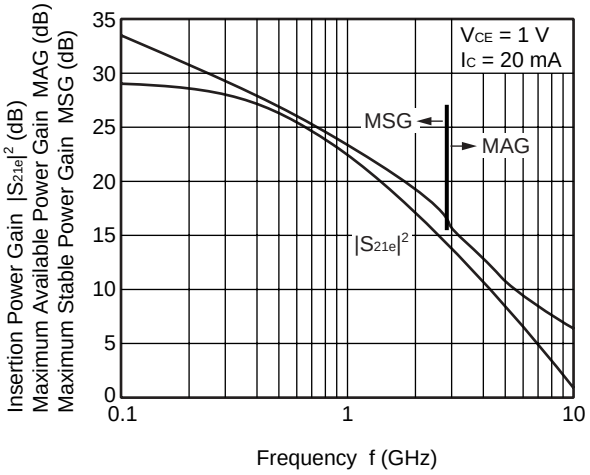
GAIN BANDWIDTH PRODUCT
vs. COLLECTOR CURRENT



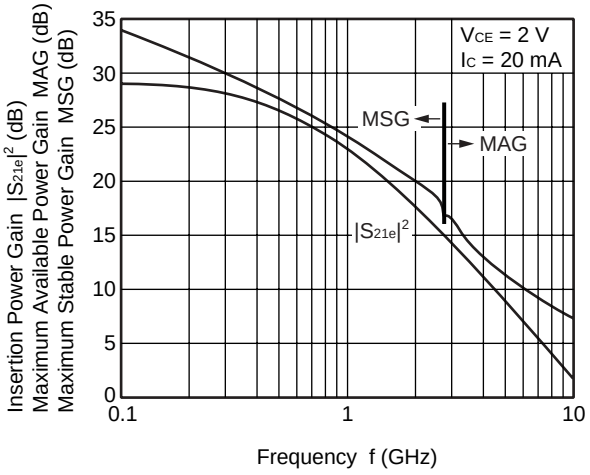
INSERTION POWER GAIN,
MAG, MSG vs. FREQUENCY



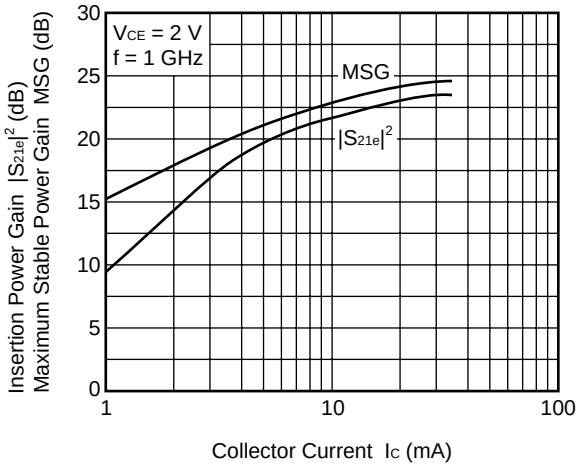
INSERTION POWER GAIN,
MAG, MSG vs. FREQUENCY



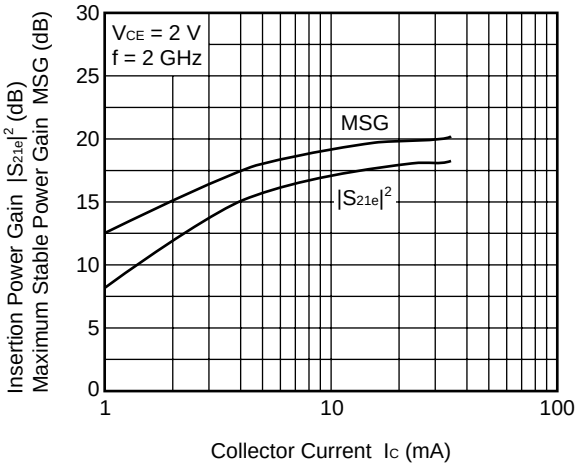
INSERTION POWER GAIN,
MAG, MSG vs. FREQUENCY



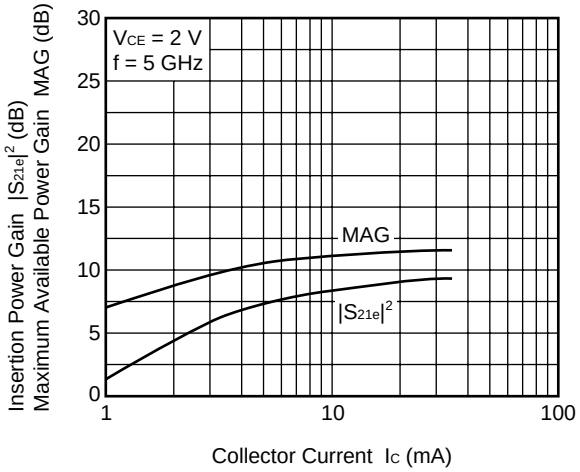
INSERTION POWER GAIN, MSG
vs. COLLECTOR CURRENT



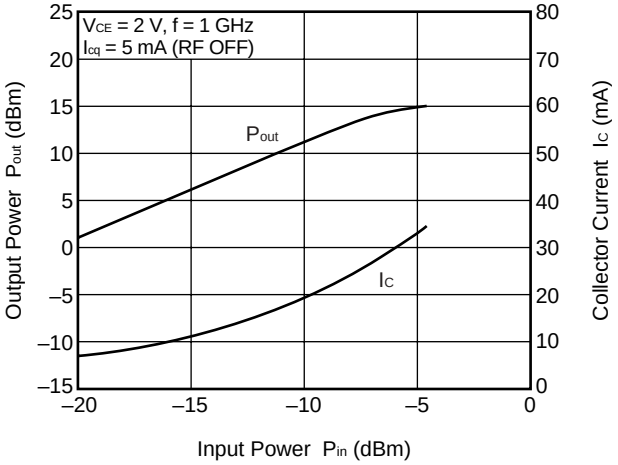
INSERTION POWER GAIN, MSG
vs. COLLECTOR CURRENT



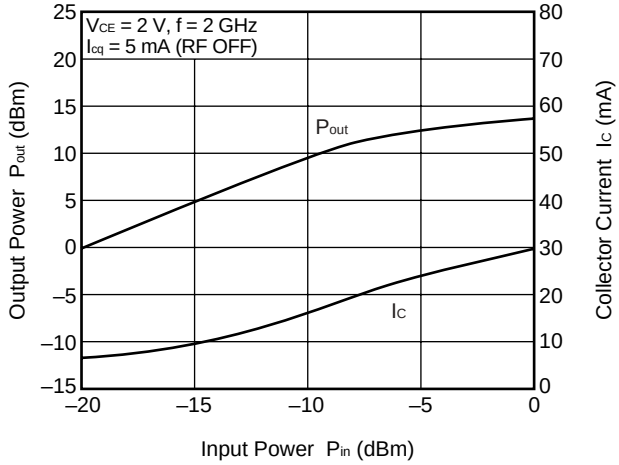
INSERTION POWER GAIN, MAG
vs. COLLECTOR CURRENT



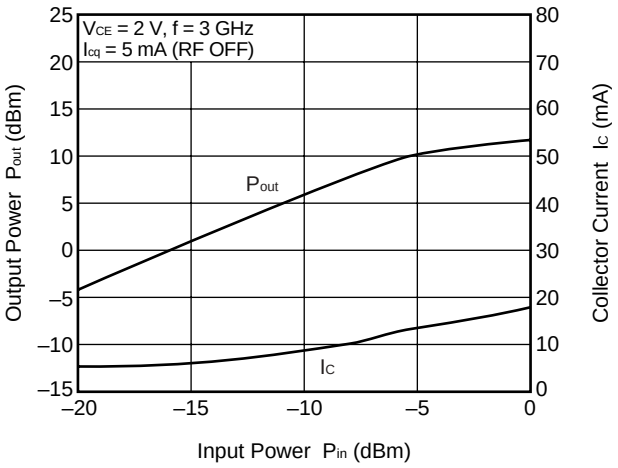
OUTPUT POWER, COLLECTOR CURRENT vs. INPUT POWER



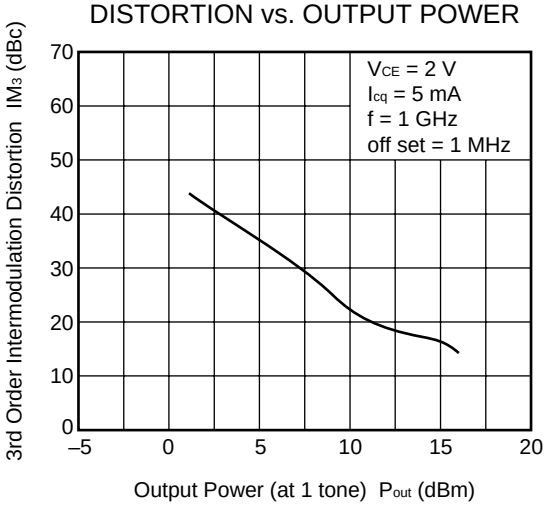
OUTPUT POWER, COLLECTOR CURRENT vs. INPUT POWER



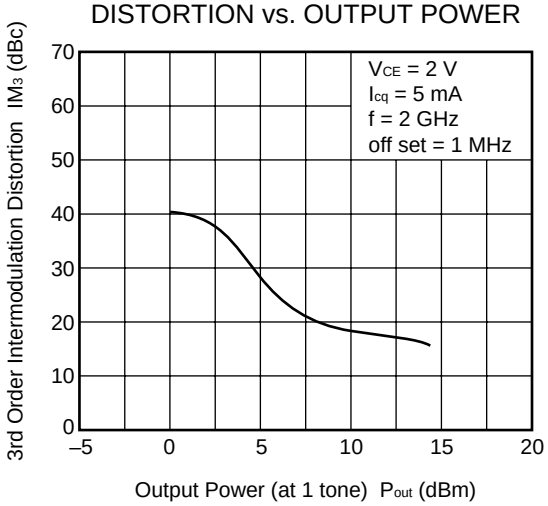
OUTPUT POWER, COLLECTOR CURRENT vs. INPUT POWER



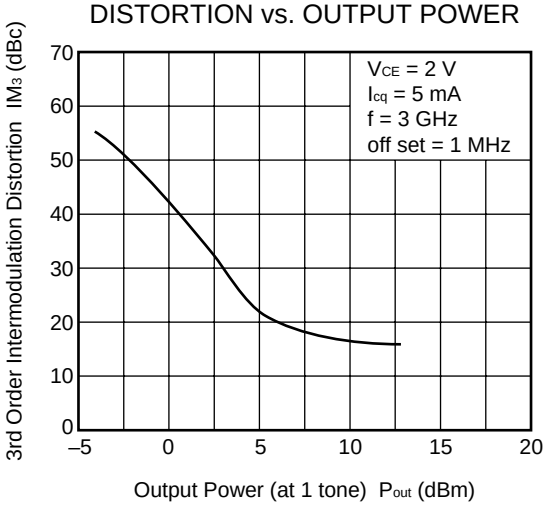
3RD ORDER INTERMODULATION DISTORTION vs. OUTPUT POWER



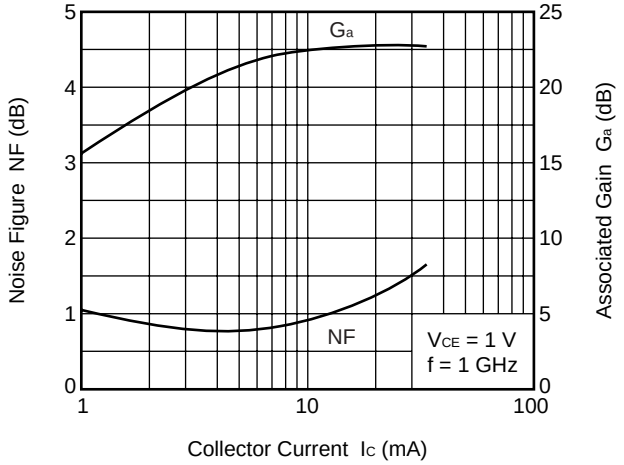
3RD ORDER INTERMODULATION DISTORTION vs. OUTPUT POWER



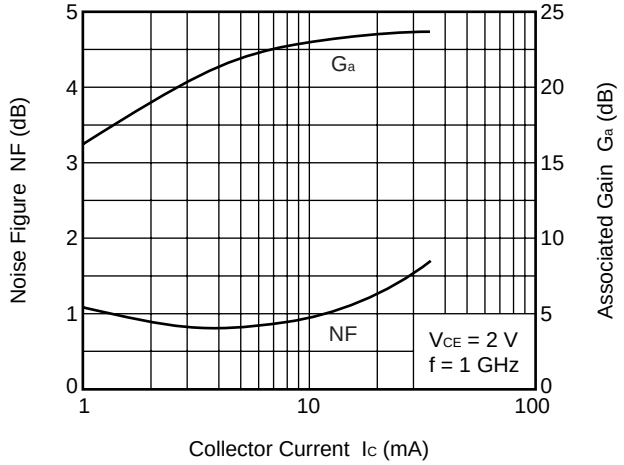
3RD ORDER INTERMODULATION DISTORTION vs. OUTPUT POWER



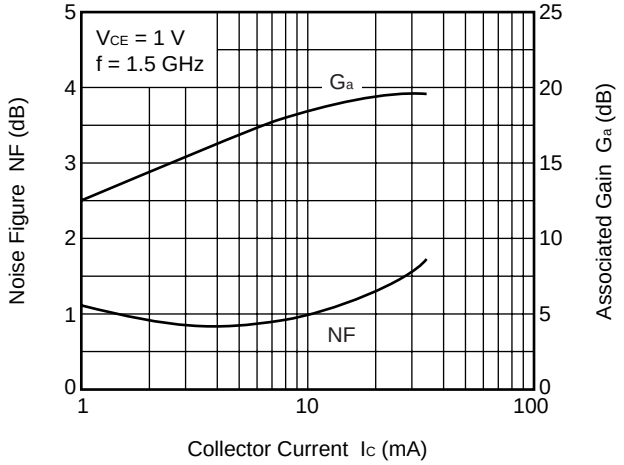
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



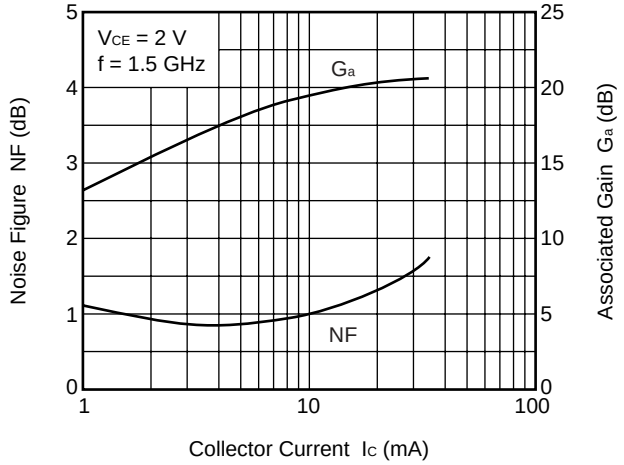
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



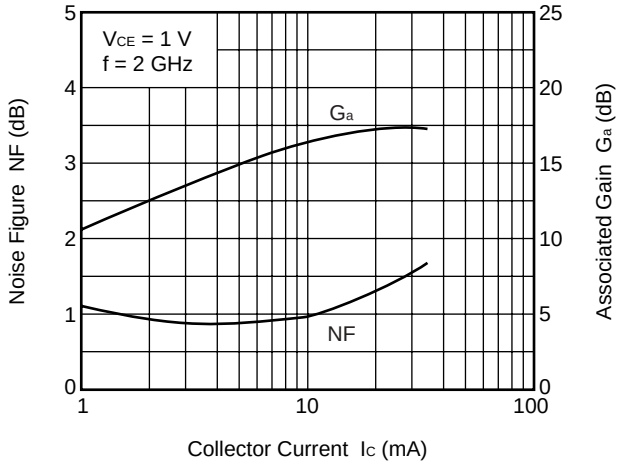
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



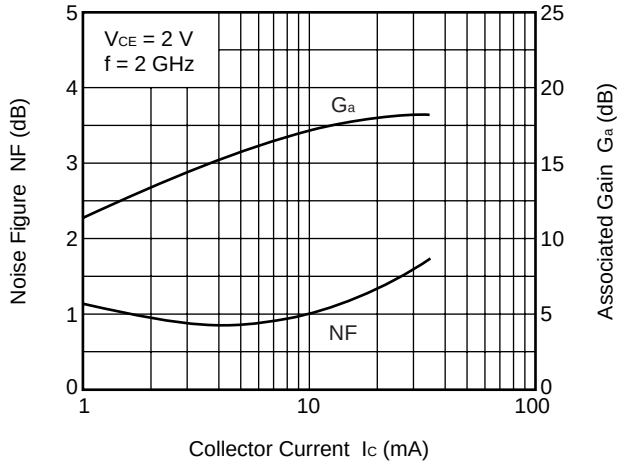
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



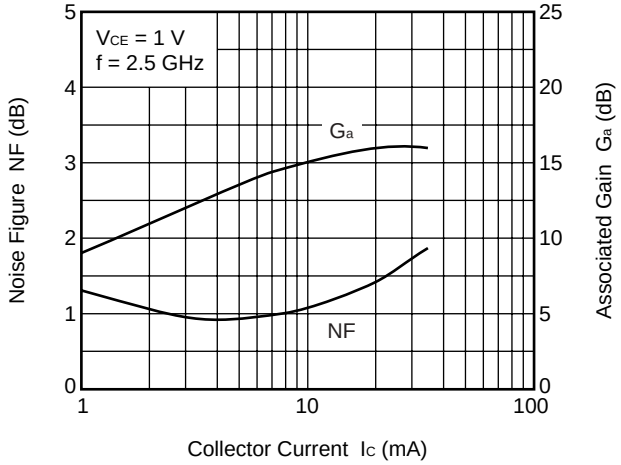
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



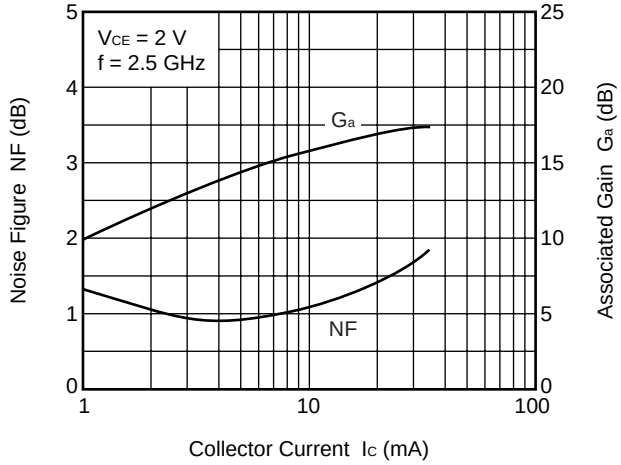
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



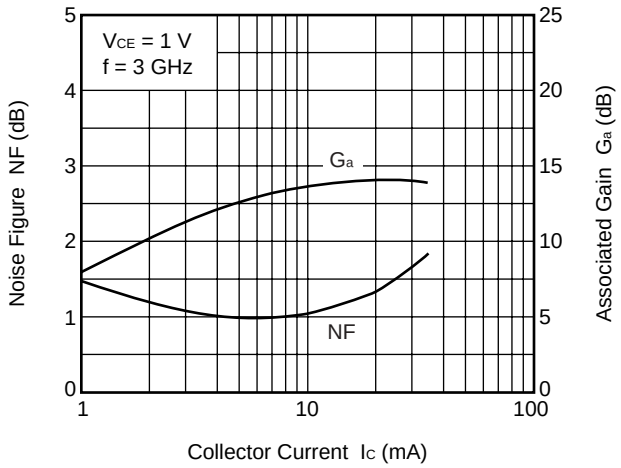
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



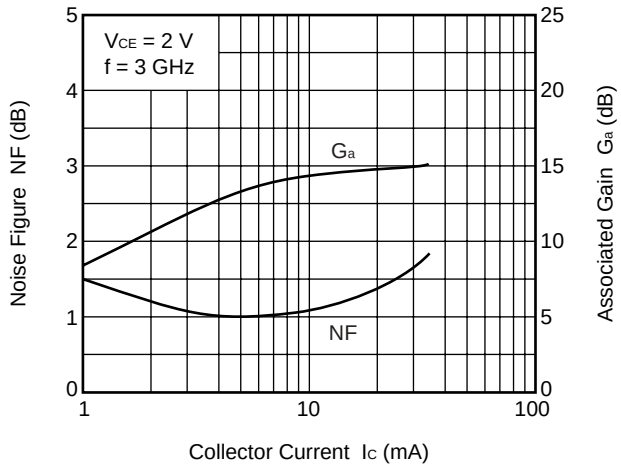
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



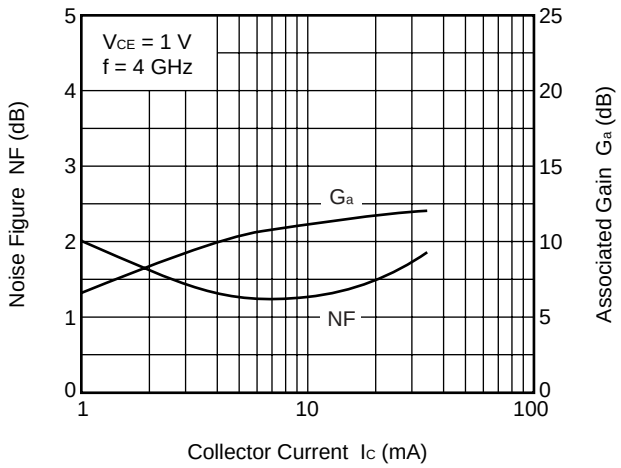
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



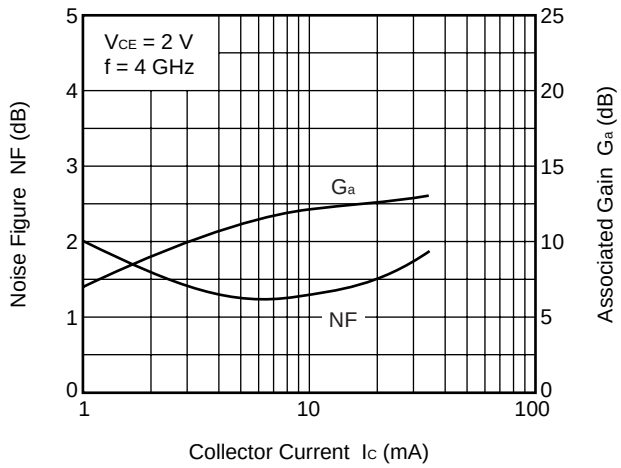
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



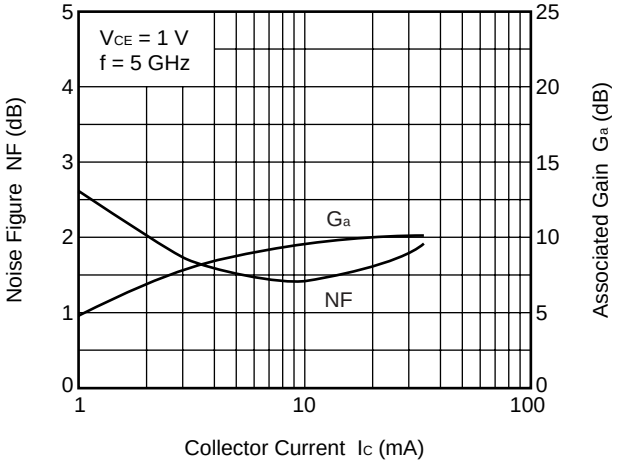
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



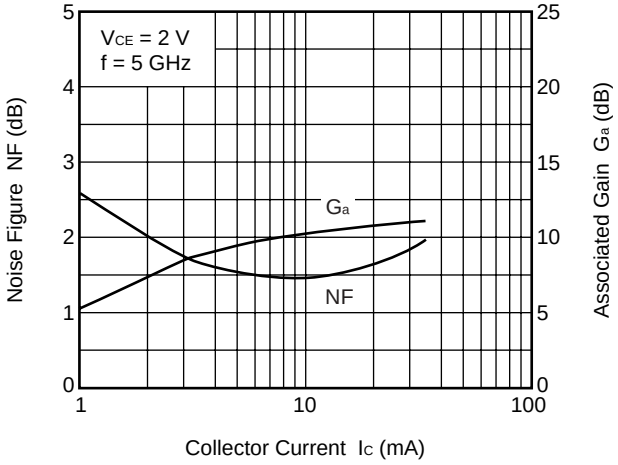
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



NOISE FIGURE, ASSOCIATED GAIN
vs. COLLECTOR CURRENT



NOISE FIGURE, ASSOCIATED GAIN
vs. COLLECTOR CURRENT



Remark The graphs indicate nominal characteristics.

S-PARAMETERS

S-parameters/Noise parameters are provided on the NEC Compound Semiconductor Devices Web site in a form (S2P) that enables direct import to a microwave circuit simulator without keyboard input.

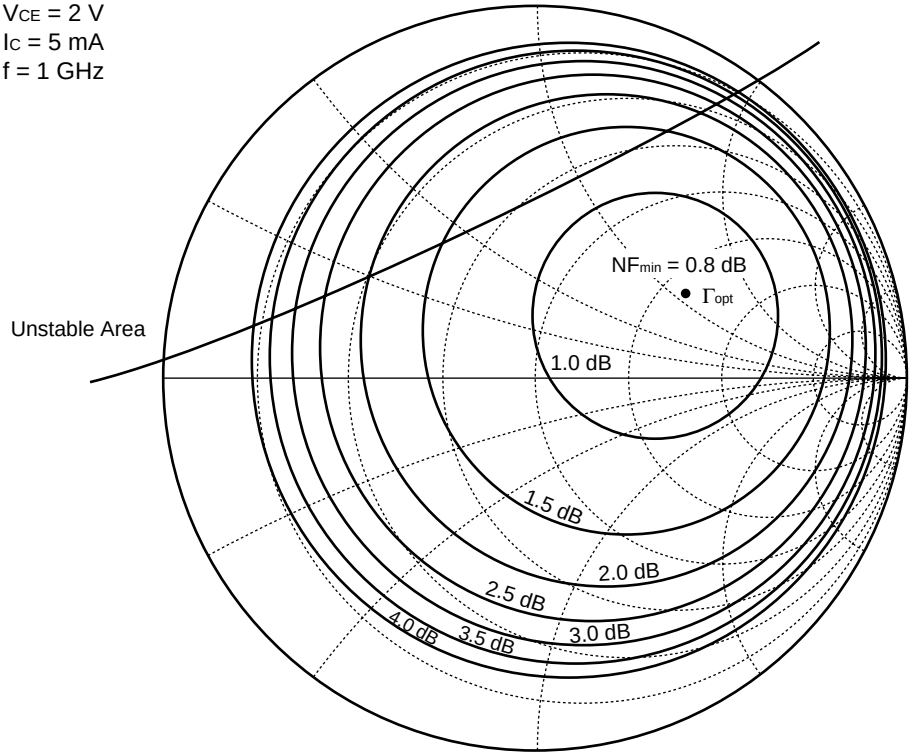
Click here to download S-parameters.

[RF and Microwave] → [Device Parameters]

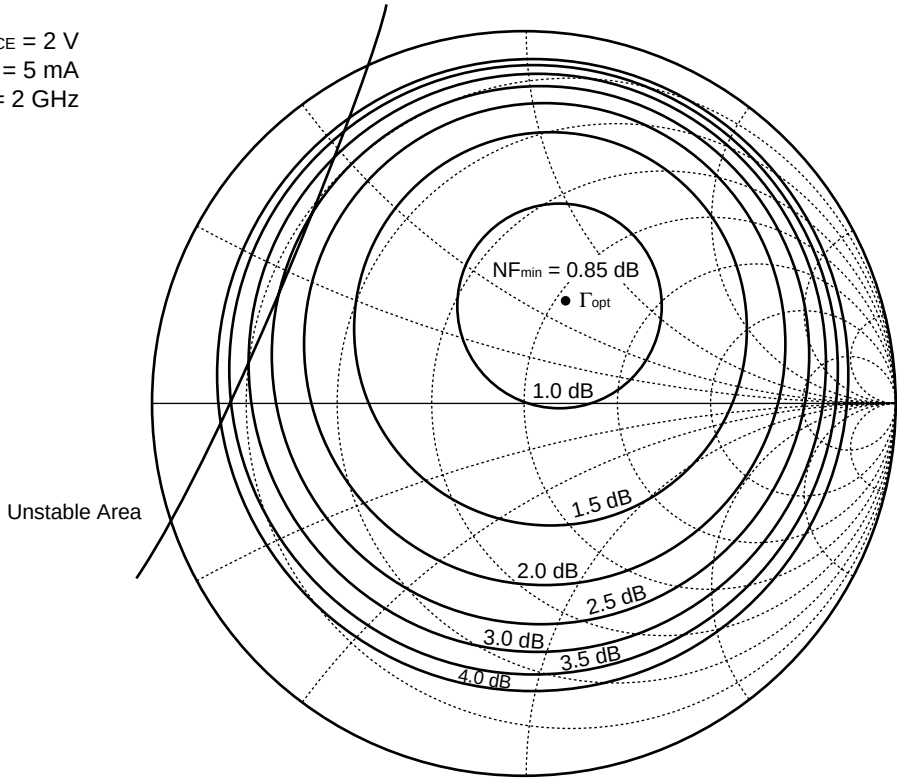
URL http://www.csd-nec.com/

EQUAL NF CIRCLE

V_{CE} = 2 V
I_C = 5 mA
f = 1 GHz

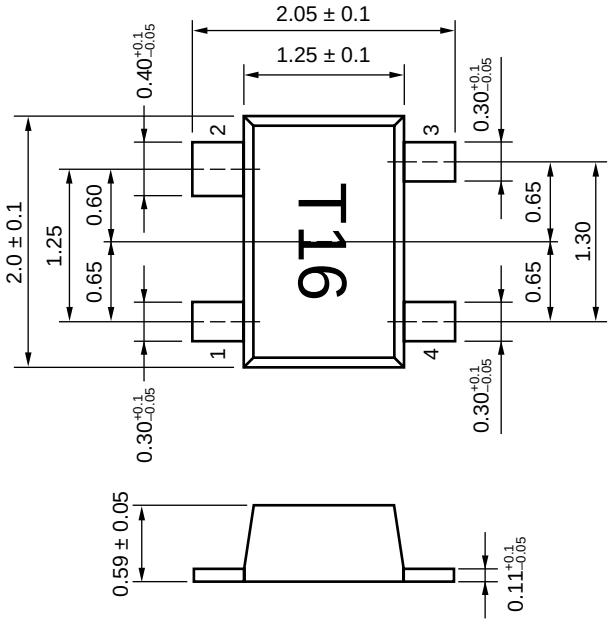


V_{CE} = 2 V
I_C = 5 mA
f = 2 GHz



PACKAGE DIMENSIONS

FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M04) (UNIT: mm)



PIN CONNECTIONS

1. Emitter
2. Collector
3. Emitter
4. Base

- **The information in this document is current as of May, 2003. The information is subject to change without notice. For actual design-in, refer to the latest publications of NEC's data sheets or data books, etc., for the most up-to-date specifications of NEC semiconductor products. Not all products and/or types are available in every country. Please check with an NEC sales representative for availability and additional information.**
- No part of this document may be copied or reproduced in any form or by any means without prior written consent of NEC. NEC assumes no responsibility for any errors that may appear in this document.
- NEC does not assume any liability for infringement of patents, copyrights or other intellectual property rights of third parties by or arising from the use of NEC semiconductor products listed in this document or any other liability arising from the use of such products. No license, express, implied or otherwise, is granted under any patents, copyrights or other intellectual property rights of NEC or others.
- Descriptions of circuits, software and other related information in this document are provided for illustrative purposes in semiconductor product operation and application examples. The incorporation of these circuits, software and information in the design of customer's equipment shall be done under the full responsibility of customer. NEC assumes no responsibility for any losses incurred by customers or third parties arising from the use of these circuits, software and information.
- While NEC endeavours to enhance the quality, reliability and safety of NEC semiconductor products, customers agree and acknowledge that the possibility of defects thereof cannot be eliminated entirely. To minimize risks of damage to property or injury (including death) to persons arising from defects in NEC semiconductor products, customers must incorporate sufficient safety measures in their design, such as redundancy, fire-containment, and anti-failure features.
- NEC semiconductor products are classified into the following three quality grades:
  "Standard", "Special" and "Specific". The "Specific" quality grade applies only to semiconductor products developed based on a customer-designated "quality assurance program" for a specific application. The recommended applications of a semiconductor product depend on its quality grade, as indicated below. Customers must check the quality grade of each semiconductor product before using it in a particular application.
  "Standard": Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots
  "Special": Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
  "Specific": Aircraft, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems and medical equipment for life support, etc.
  The quality grade of NEC semiconductor products is "Standard" unless otherwise expressly specified in NEC's data sheets or data books, etc. If customers wish to use NEC semiconductor products in applications not intended by NEC, they must contact an NEC sales representative in advance to determine NEC's willingness to support a given application.
  (Note)
  (1) "NEC" as used in this statement means NEC Corporation, NEC Compound Semiconductor Devices, Ltd. and also includes its majority-owned subsidiaries.
  (2) "NEC semiconductor products" means any semiconductor product developed or manufactured by or for NEC (as defined above).

M8E 00.4-0110

▶**For further information, please contact**

NEC Compound Semiconductor Devices, Ltd.
5th Sales Group, Sales Division TEL: +81-44-435-1588 FAX: +81-44-435-1579 E-mail: salesinfo@csd-nec.com

NEC Compound Semiconductor Devices Hong Kong Limited
Hong Kong Head Office TEL: +852-3107-7303 FAX: +852-3107-7309 E-mail: ncsd-hk@elhk.nec.com.hk
Taipei Branch Office TEL: +886-2-8712-0478 FAX: +886-2-2545-3859
Korea Branch Office TEL: +82-2-558-2120 FAX: +82-2-558-5209

NEC Electronics (Europe) GmbH http://www.ee.nec.de/
TEL: +49-211-6503-01 FAX: +49-211-6503-487

California Eastern Laboratories, Inc. http://www.cel.com/
TEL: +1-408-988-3500 FAX: +1-408-988-0279

0302-1